

# FDD6680

## N-Channel Logic Level PWM Optimized PowerTrench™ MOSFET

### General Description

This N-Channel Logic level MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

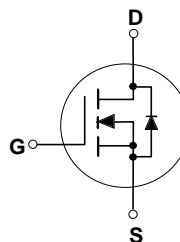
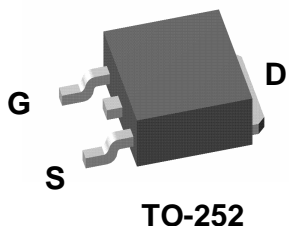
The MOSFET features faster switching and lower gate charge than other MOSFETs with comparable  $R_{DS(on)}$  specifications. The result is a MOSFET that is easier to drive, even at very high frequencies, and DC/DC power supply designs with higher overall efficiency.

### Features

- 55 A, 30 V.  $R_{DS(on)} = 0.010 \Omega @ V_{GS} = 10 \text{ V}$   
 $R_{DS(on)} = 0.015 \Omega @ V_{GS} = 4.5 \text{ V}$ .
- Optimized for use in high frequency DC/DC converters.
- Low gate charge (19nC typical).
- Very Fast switching.

### Applications

- DC/DC converter
- Motor drives



### Absolute Maximum Ratings

$T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain-Source Voltage	30	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Maximum Drain Current -Continuous (Note 1) (Note 1a)	55 14	A
	Maximum Drain Current -Pulsed	100	
$P_D$	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$ (Note 1)	60	W
	$T_A = 25^\circ\text{C}$ (Note 1a)	3.2	
	$T_A = 25^\circ\text{C}$ (Note 1b)	1.3	
$T_J, T_{stg}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to- Case (Note 1)	2.1	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to- Ambient (Note 1a) (Note 1b)	40	$^\circ\text{C}/\text{W}$
		96	$^\circ\text{C}/\text{W}$

### Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDD6680	FDD6680	13"	16mm	2500

## Electrical Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Drain-Source Avalanche ratings (Note 2)

$W_{DSS}$	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 15\text{ V}, I_L = 55\text{ A}$			170	mJ
$I_{AR}$	Maximum Drain-Source Avalanche Current				55	A

### Off Characteristics

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		18		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$			-100	nA

### On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1	2	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		-5.5		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 14\text{ A}$ $V_{GS} = 10\text{ V}, I_D = 14\text{ A}, T_J = 125^\circ\text{C}$ $V_{GS} = 4.5\text{ V}, I_D = 12\text{ A}$		0.008 0.013 0.012	0.010 0.017 0.015	$\Omega$
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 5\text{ V}$	50			A
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{ V}, I_D = 14\text{ A}$		38		S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 15\text{ V},$		2070		pF
$C_{oss}$	Output Capacitance	$V_{GS} = 0\text{ V},$		510		pF
$C_{rss}$	Reverse Transfer Capacitance	$f = 1.0\text{ MHz}$		235		pF

### Switching Characteristics (Note 2)

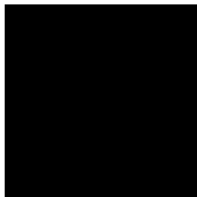
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15\text{ V}, I_D = 1\text{ A},$		15	28	ns
$t_r$	Turn-On Rise Time	$V_{GS} = 10\text{ V}, R_{GEN} = 6\ \Omega$		18	33	ns
$t_{d(off)}$	Turn-Off Delay Time			40	64	ns
$t_f$	Turn-Off Fall Time			18	33	ns
$Q_g$	Total Gate Charge	$V_{DS} = 15\text{ V}, I_D = 14\text{ A},$		19	27	nC
$Q_{gs}$	Gate-Source Charge	$V_{GS} = 5\text{ V},$		7		nC
$Q_{gd}$	Gate-Drain Charge			6		nC

### Drain-Source Diode Characteristics and Maximum Ratings

$I_S$	Maximum Continuous Drain-Source Diode Forward Current				2.3	A
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 2.3\text{ A}$ (Note 2)		0.75	1.2	V

#### Notes:

- $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the drain tab.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



■ a)  $R_{\theta JA} = 40^\circ\text{C/W}$  when mounted on a  $1\text{ in}^2$  pad of 2oz copper.

■ b)  $R_{\theta JA} = 96^\circ\text{C/W}$  on a minimum mounting pad.

Scale 1 : 1 on letter size paper

- Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

Typical Characteristics

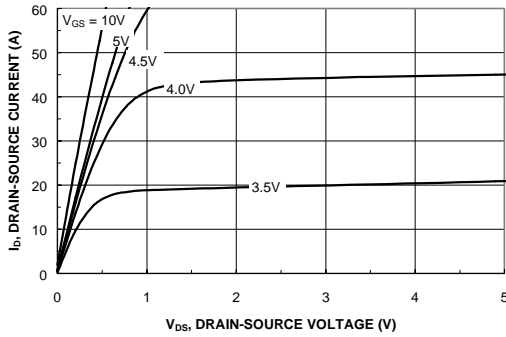


Figure 1. On-Region Characteristics.

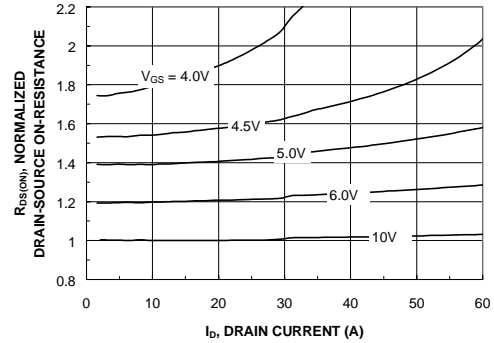


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

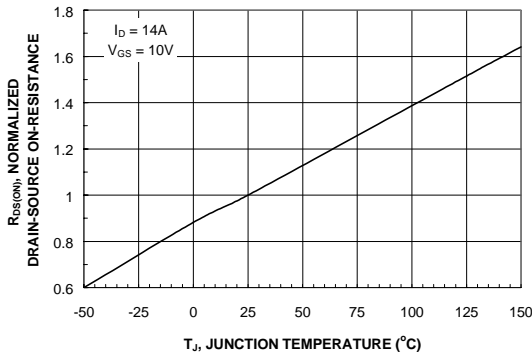


Figure 3. On-Resistance Variation with Temperature.

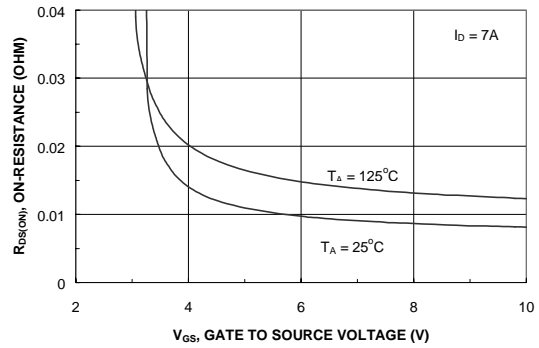


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

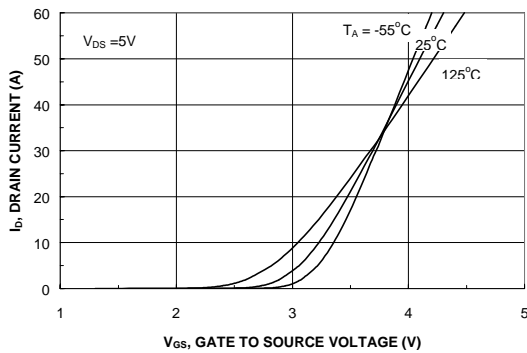


Figure 5. Transfer Characteristics.

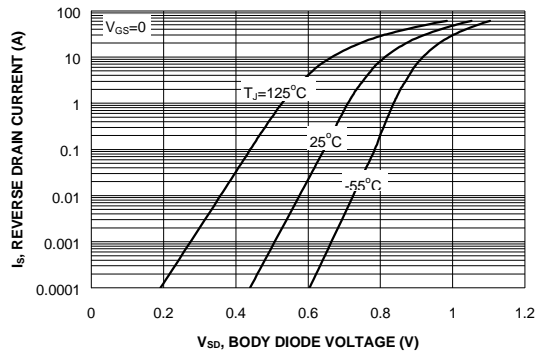


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)

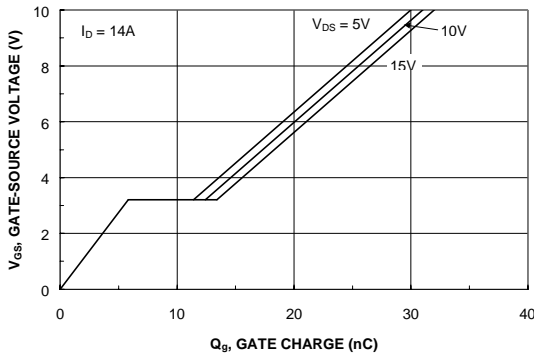


Figure 7. Gate-Charge Characteristics.

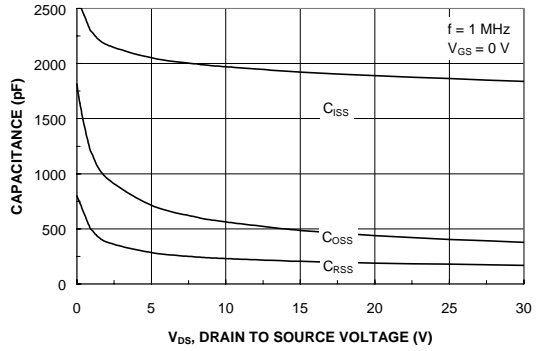


Figure 8. Capacitance Characteristics.

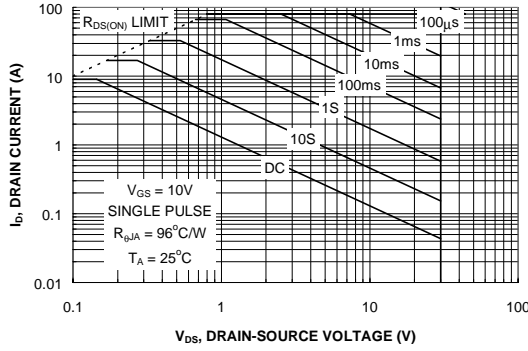


Figure 9. Maximum Safe Operating Area.

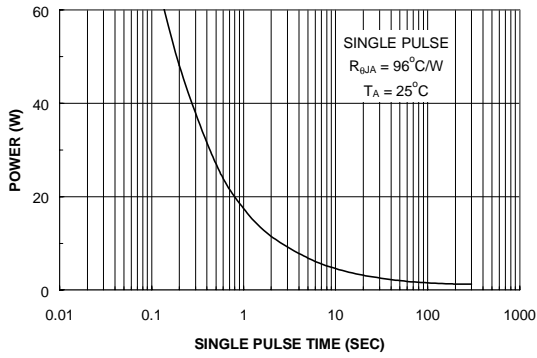


Figure 10. Single Pulse Maximum Power Dissipation.

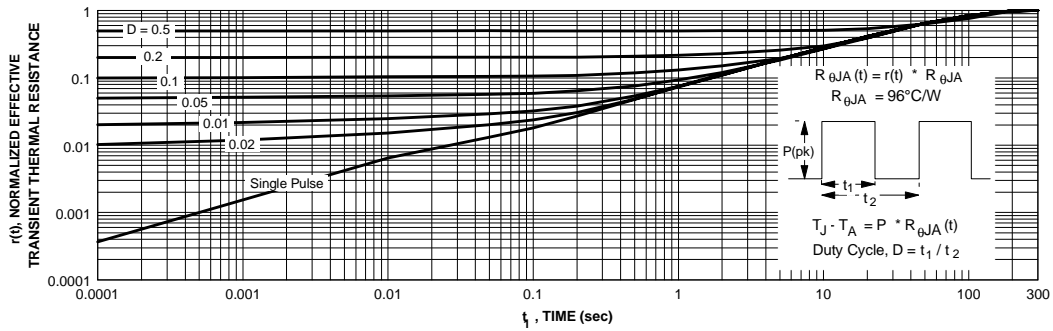


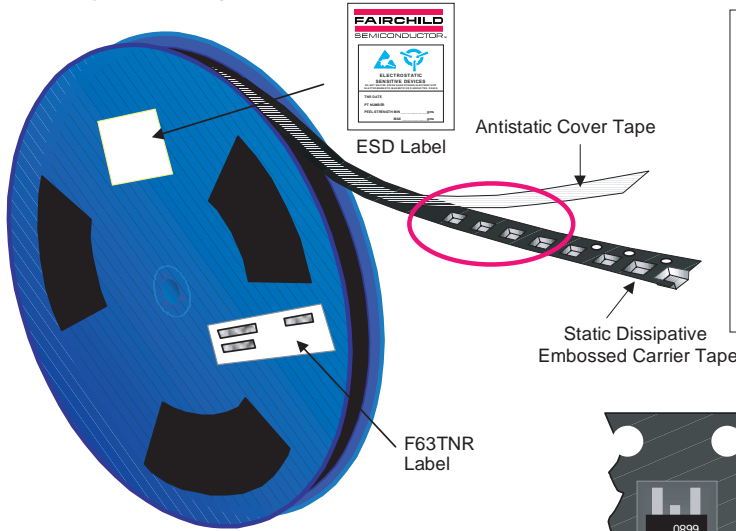
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

# TO-252 Tape and Reel Data and Package Dimensions



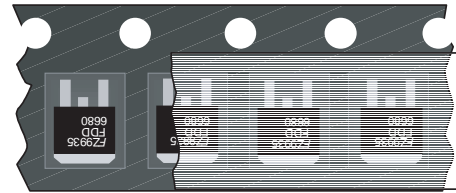
## D-PAK (TO-252) Packaging Configuration: Figure 1.0



### Packaging Description:

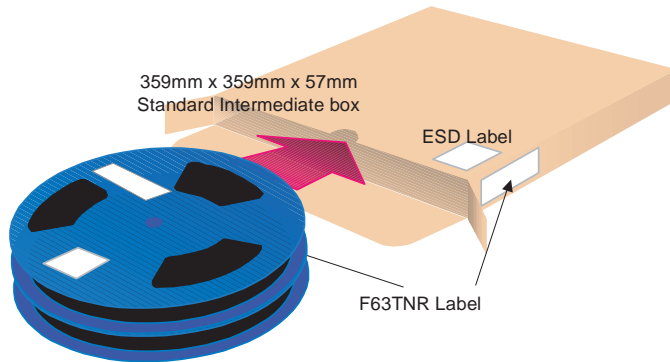
TO-252 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2500 units per 13" or 330mm diameter reel. The reels are dark blue in color and is made of polystyrene plastic (anti-static coated). This and some other options are further described in the Packaging Information table.

These full reels are individually barcode labeled and placed inside a standard intermediate box (illustrated in figure 1.0) made of recyclable corrugated brown paper. One box contains two reels maximum. And these boxes are placed inside a barcode labeled shipping box which comes in different sizes depending on the number of parts shipped.

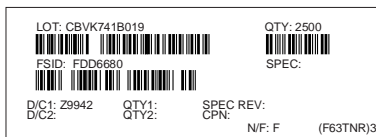


D-PAK (TO-252) Unit Orientation

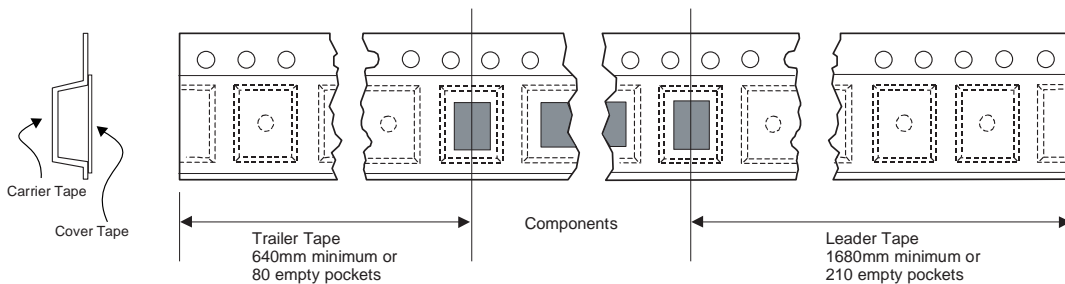
D-PAK (TO-252) Packaging Information	
Packaging Option	Standard (no flow code)
Packaging type	TNR
Qty per Reel/Tube/Bag	2,500
Reel Size	13" Dia
Box Dimension (mm)	359x359x57
Max qty per Box	5,000
Weight per unit (gm)	0.300
Weight per Reel(kg)	1.200
Note/Comments	



### F63TNR Label sample

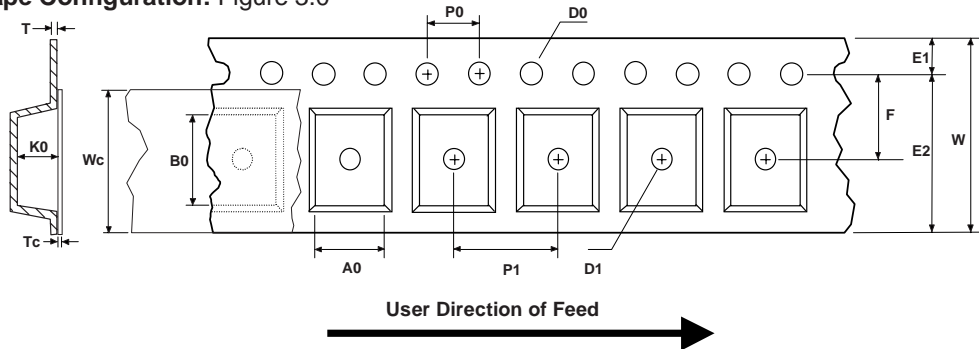


## TO-252 (D-PAK) Tape Leader and Trailer Configuration: Figure 2.0



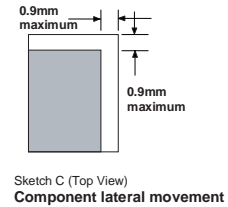
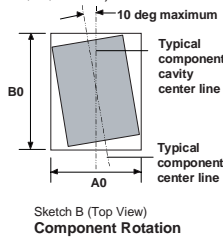
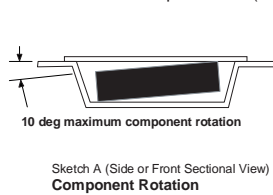
# TO-252 Tape and Reel Data and Package Dimensions

## D-PAK (TO-252) Embossed Carrier Tape Configuration: Figure 3.0

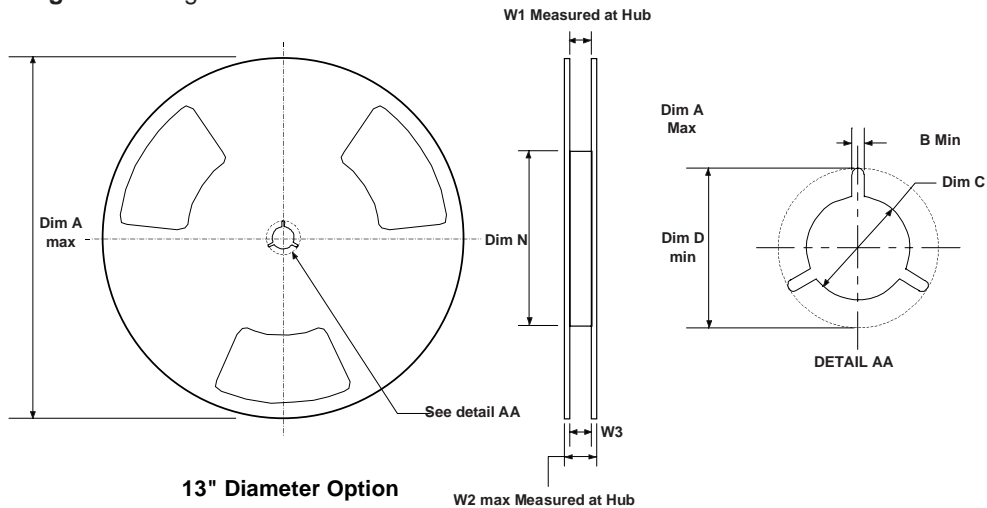


Dimensions are in millimeter														
Pkg type	A0	B0	W	D0	D1	E1	E2	F	P1	P0	K0	T	Wc	Tc
TO252 (24mm)	6.90 +/-0.10	10.50 +/-0.10	16.0 +/-0.3	1.55 +/-0.05	1.5 +/-0.10	1.75 +/-0.10	14.25 min	7.50 +/-0.10	8.0 +/-0.1	4.0 +/-0.1	2.65 +/-0.10	0.30 +/-0.05	13.0 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



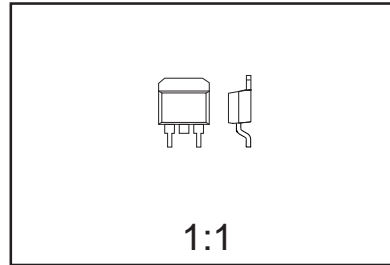
## D-PAK (TO-252) Reel Configuration: Figure 4.0



Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
164mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.646 +0.078/-0.000 16.4 +2/0	0.882 22.4	0.626 - 0.764 15.9 - 19.4

# TO-252 Tape and Reel Data and Package Dimensions

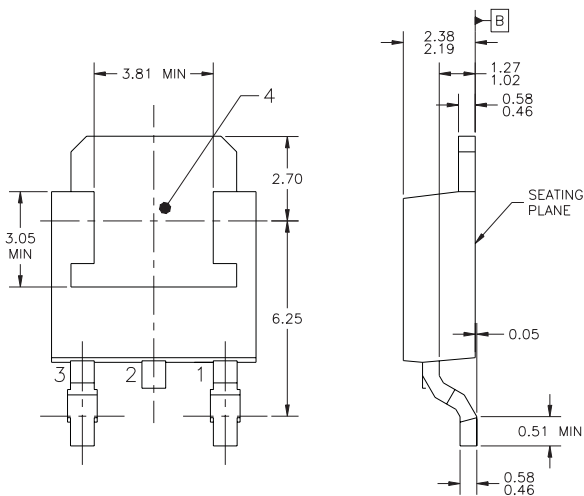
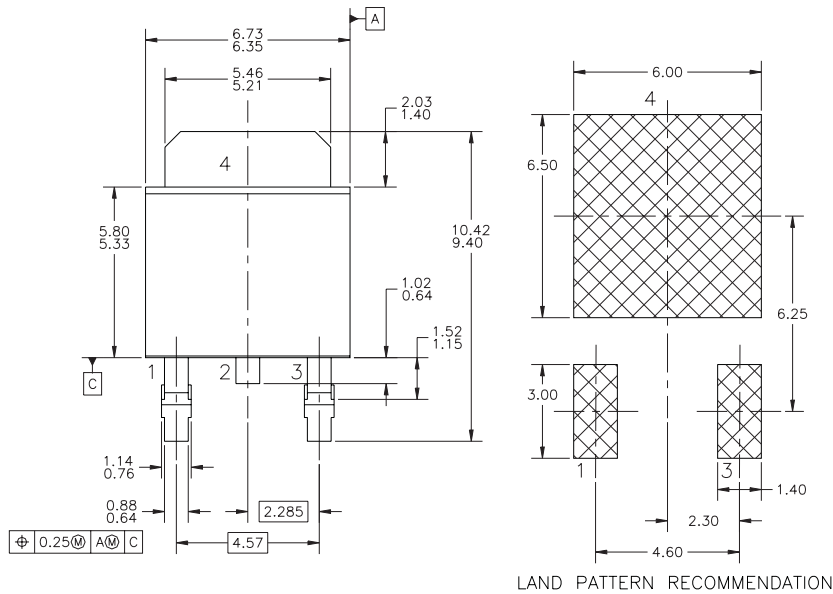
## TO-252 (FS PKG Code AA)



Scale 1:1 on letter size paper

Dimensions shown below are in:  
inches [millimeters]

Part Weight per unit (gram): 0.300



NOTES: UNLESS OTHERWISE SPECIFIED

A) ALL DIMENSIONS ARE IN MILLIMETERS.

B) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE B, VARIATION AB, ITEM 10.268, DATED SEPTEMBER 1988.

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E <sup>2</sup> CMOS™	PowerTrench®	VCX™
FACT™	QFET™	
FACT Quiet Series™	QS™	
FAST®	Quiet Series™	
FASTr™	SuperSOT™-3	
GTO™	SuperSOT™-6	
HiSeC™	SuperSOT™-8	

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## PRODUCT STATUS DEFINITIONS

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